BLC8G27LS-100AV

Power LDMOS transistor

Rev. 2 — 29 September 2014 Product data sheet

1. Product profile

1.1 General description

100 W LDMOS packaged asymmetrical Doherty power transistor for base station applications at frequencies from 2496 MHz to 2690 MHz.

Table 1. Typical performance

Typical RF performance at T_{case} = 25 °C in the Doherty demo board.

Test signal	f	V_{DS}	$P_{L(AV)}$	G_p	η_D	ACPR
	(MHz)	(V)	(W)	(dB)	(%)	(dBc)
1-carrier W-CDMA	2520 to 2620	28	18	15.5	45	–30 [1]

[1] Test signal: 3GPP test model 1; 1 to 64 DPCH; PAR = 7.2 dB at 0.01 % probability on CCDF.

1.2 Features and benefits

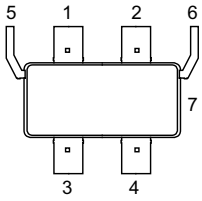
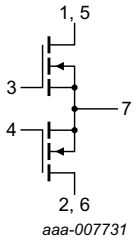
- Excellent ruggedness
- High efficiency
- Low thermal resistance providing excellent thermal stability
- Decoupling leads to enable improved video bandwidth
- Lower output capacitance for improved performance in Doherty applications
- Designed for low memory effects providing excellent pre-distortability
- Internally matched for ease of use
- Integrated ESD protection
- Compliant to Directive 2002/95/EC, regarding Restriction of Hazardous Substances (RoHS)

1.3 Applications

- RF power amplifier for LTE base stations and multi carrier applications in the 2496 MHz to 2690 MHz frequency range

2. Pinning information

Table 2. Pinning

Pin	Description	Simplified outline	Graphic symbol
1	drain1 (main)		
2	drain2 (peak)		
3	gate1 (main)		
4	gate2 (peak)		
5	video decoupling (main)		
6	video decoupling (peak)		
7	source [1]		

[1] Connected to flange.

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BLC8G27LS-100AV	-	air cavity plastic earless flanged package; 6 leads	SOT1275-1

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage		-	65	V
V_{GS}	gate-source voltage		−0.5	+13	V
T_{stg}	storage temperature		−65	+150	°C
T_j	junction temperature	[1]	-	225	°C

[1] Continuous use at maximum temperature will affect the reliability, for details refer to the on-line MTF calculator.

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Typ	Unit
$R_{th(j\text{-}case)}$	thermal resistance from junction to case	T_{case} = 80 °C; V_{DS} = 28 V; I_{Dq} = 250 mA		
		P_L = 18 W	0.314	K/W
		P_L = 65 W	0.289	K/W

6. Characteristics

Table 6. DC characteristics

T_j = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Main device						
$V_{(BR)DSS}$	drain-source breakdown voltage	V_{GS} = 0 V; I_D = 0.51 mA	65	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	V_{DS} = 10 V; I_D = 51 mA	1.5	1.9	2.3	V
V_{GSq}	gate-source quiescent voltage	V_{DS} = 28 V; I_D = 306 mA	1.7	2.0	2.5	V
I_{DSS}	drain leakage current	V_{GS} = 0 V; V_{DS} = 28 V	-	-	1.4	µA
I_{DSX}	drain cut-off current	V_{GS} = $V_{GS(th)}$ + 3.75 V; V_{DS} = 10 V	-	9.6	-	A
I_{GSS}	gate leakage current	V_{GS} = 11 V; V_{DS} = 0 V	-	-	140	nA
g_{fs}	forward transconductance	V_{DS} = 10 V; I_D = 51 mA	-	0.46	-	S
$R_{DS(on)}$	drain-source on-state resistance	V_{GS} = $V_{GS(th)}$ + 3.75 V; I_D = 1.785 A	-	294	451	mΩ
Peak device						
$V_{(BR)DSS}$	drain-source breakdown voltage	V_{GS} = 0 V; I_D = 0.72 mA	65	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	V_{DS} = 10 V; I_D = 72 mA	1.5	1.9	2.3	V
V_{GSq}	gate-source quiescent voltage	V_{DS} = 28 V; I_D = 432 mA	1.7	2.0	2.5	V
I_{DSS}	drain leakage current	V_{GS} = 0 V; V_{DS} = 28 V	-	-	1.4	µA
I_{DSX}	drain cut-off current	V_{GS} = $V_{GS(th)}$ + 3.75 V; V_{DS} = 10 V	-	13.4	-	A
I_{GSS}	gate leakage current	V_{GS} = 11 V; V_{DS} = 0 V	-	-	140	nA
g_{fs}	forward transconductance	V_{DS} = 10 V; I_D = 72 mA	-	0.62	-	S
$R_{DS(on)}$	drain-source on-state resistance	V_{GS} = $V_{GS(th)}$ + 3.75 V; I_D = 2.52 A	-	210	323	mΩ

Table 7. RF characteristics

Test signal: 1-carrier W-CDMA; PAR = 7.2 dB at 0.01 % probability on the CCDF; 3GPP test model 1; 1 to 64 DPCH; f_1 = 2496 MHz; f_2 = 2690 MHz; RF performance at V_{DS} = 28 V; I_{Dq} = 250 mA (main); $V_{GS(amp)peak}$ = 0.8 V; T_{case} = 25 °C; unless otherwise specified; in an asymmetrical Doherty production test circuit at 2496 MHz to 2690 MHz.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
G_p	power gain	$P_{L(AV)}$ = 17.8 W	14.3	15.5	-	dB
RL_{in}	input return loss	$P_{L(AV)}$ = 17.8 W	-	–10	–6	dB
η_D	drain efficiency	$P_{L(AV)}$ = 17.8 W	39	44	-	%
ACPR	adjacent channel power ratio	$P_{L(AV)}$ = 17.8 W	-	–31	–25	dBc

Table 8. RF characteristics

Test signal: 1-carrier W-CDMA; PAR = 7.2 dB at 0.01 % probability on the CCDF; 3GPP test model 1; 1 to 64 DPCH; f = 2690 MHz; RF performance at V_{DS} = 28 V; I_{Dq} = 250 mA (main); $V_{GS(amp)peak}$ = 0.8 V; T_{case} = 25 °C; unless otherwise specified; in an asymmetrical Doherty production test circuit at 2496 MHz to 2690 MHz.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
PAR_O	output peak-to-average ratio	$P_{L(AV)}$ = 50 W	3.6	4.2	-	dB
$P_{L(M)}$	peak output power		112	133	-	W

7. Test information

7.1 Ruggedness in Doherty operation

The BLC8G27LS-100AV is capable of withstanding a load mismatch corresponding to a VSWR = 10 : 1 through all phases under the following conditions: V_{DS} = 28 V; I_{Dq} = 250 mA (main); $V_{GS(amp)peak}$ = 0.8 V; P_L = 70 W (CW); f = 2496 MHz.

7.2 Impedance information

Table 9. Typical impedance of main device

Measured load-pull data of main device; I_{Dq} = 300 mA (main); V_{DS} = 28 V.

f	Z_S [1]	Z_L [1]	P_L [2]	η_D [2]	G_p [2]
(MHz)	(Ω)	(Ω)	(W)	(%)	(dB)
Maximum power load					
2496	2.5 – j6.7	4.0 – j7.6	63	56.0	16.0
2600	3.4 – j7.0	4.0 – j7.6	61	55.6	16.7
2690	3.2 – j6.2	4.0 – j7.6	60	56.1	17.1
Maximum drain efficiency load					
2496	2.5 – j6.7	7.1 – j5.1	47.9	64	18.2
2600	3.4 – j7.0	6.5 – j4.6	44.3	63	19.0
2690	3.2 – j6.2	6.0 – j4.1	40.5	62	19.5

[1] Z_S and Z_L defined in Figure 1.

[2] at 3 dB gain compression.

Table 10. Typical impedance of peak device

Measured load-pull data of peak device; I_{Dq} = 400 mA (main); V_{DS} = 28 V.

f	Z_S [1]	Z_L [1]	P_L [2]	η_D [2]	G_p [2]
(MHz)	(Ω)	(Ω)	(W)	(%)	(dB)
Maximum power load					
2496	2.6 – j6.4	2.7 – j7.1	83	55.7	17.8
2600	3.2 – j6.9	2.1 – j7.1	82	51.4	17.7
2690	4.3 – j7.8	2.1 – j7.1	82	53.2	18.4
Maximum drain efficiency load					
2496	2.6 – j6.4	4.0 – j5.6	61	66.6	19.7
2600	3.2 – j6.9	3.7 – j5.1	62	60.8	20.1
2690	4.3 – j7.8	3.3 – j5.4	61	60.5	20.6

[1] Z_S and Z_L defined in Figure 1.

[2] at 3 dB gain compression.

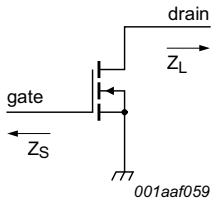


Fig 1. Definition of transistor impedance

7.3 Recommended impedances for Doherty design

Table 11. Typical impedance of main device at 1 : 1 load

Measured load-pull data of main device; I_{Dq} = 300 mA (main); V_{DS} = 28 V.

f	Z_S [1]	Z_L [1]	P_L [2]	η_D [3]	G_p [3]
(MHz)	**(Ω)**	**(Ω)**	**(dBm)**	**(%)**	**(dB)**
2496	2.5 – j6.7	5.1 – j6.5	59	36.8	20.0
2600	3.4 – j7.0	5.1 – j6.5	56	38.0	20.5
2690	3.2 – j6.2	5.1 – j6.5	56	39.2	21.2

[1] Z_S and Z_L defined in Figure 1.

[2] at 3 dB gain compression.

[3] at $P_{L(AV)}$ = 42.5 dBm.

Table 12. Typical impedance of main device at 1 : 2.5 load

Measured load-pull data of main device; I_{Dq} = 300 mA (main); V_{DS} = 28 V.

f	Z_S [1]	Z_L [1]	P_L [2]	η_D [3]	G_p [3]
(MHz)	**(Ω)**	**(Ω)**	**(dBm)**	**(%)**	**(dB)**
2496	2.5 – j6.7	11.2 – j2.7	31	52.0	22.2
2600	3.4 – j7.0	10.0 – j2.3	30	51.1	22.5
2690	3.2 – j6.2	7.5 – j0.8	25	52.2	22.1

[1] Z_S and Z_L defined in Figure 1.

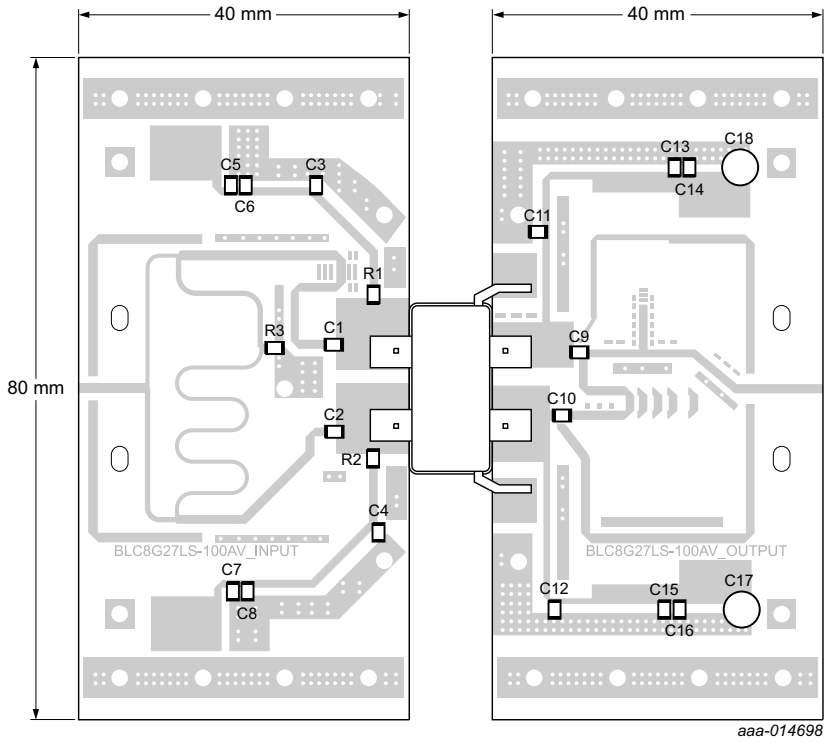
[2] at 3 dB gain compression.

[3] at $P_{L(AV)}$ = 42.5 dBm.

7.4 VBW in Doherty operation

The BLC8G27LS-100AV shows 130 MHz (typical) video bandwidth in Doherty demo board in 2600 MHz at V_{DS} = 28 V; I_{Dq} = 250 mA and $V_{GS(amp)peak}$ = 0.8 V.

7.5 Test circuit



Printed-Circuit Board (PCB): Rogers RO4350B; ε_r = 3.5; thickness = 0.508 mm; thickness copper plating = 35 μm.

See Table 13 for a list of components.

Fig 2. Component layout

Table 13. List of components

See Figure 2 for component layout.

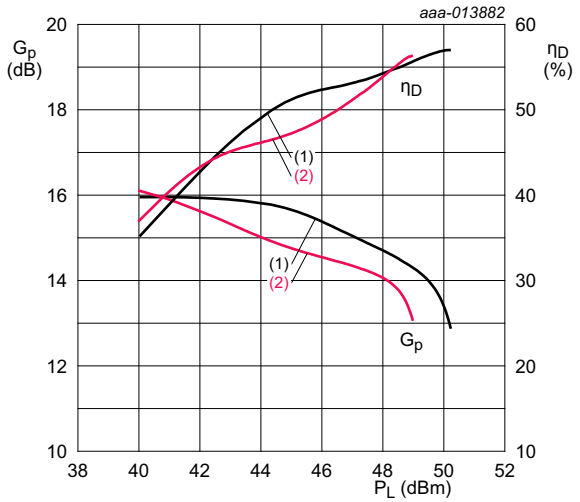
Component	Description	Value	Remarks
C1, C2, C3, C4, C10, C11, C12	multilayer ceramic chip capacitor	11 pF [1]	ATC 600F
C9	multilayer ceramic chip capacitor	5.1 pF [1]	ATC 600F
C6, C8, C13, C15	multilayer ceramic chip capacitor	1 μF, 50 V [2]	Murata
C5, C7, C14, C16	multilayer ceramic chip capacitor	10 μF, 50 V [2]	Murata
C17, C18	electrolytic capacitor	470 μF, 50 V	
R1, R2	SMD resistor	9.1 Ω	SMD 0805
R3	SMD resistor	50 Ω	SMD 0805

[1] American Technical Ceramics type 600F or capacitor of same quality

[2] Murata or capacitor of same quality

7.6 Graphical data

7.6.1 CW



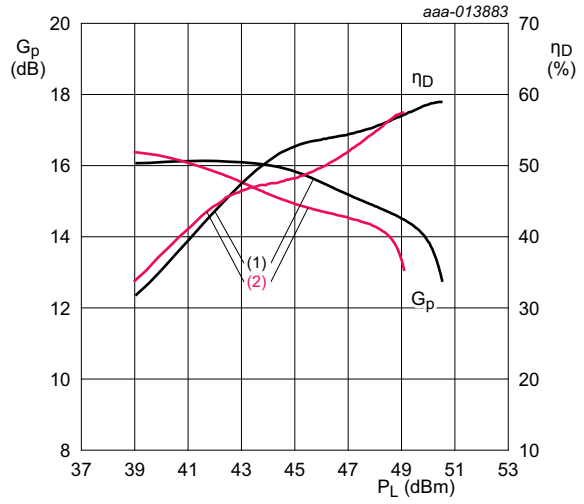
V_{DS} = 28 V; I_{Dq} = 250 mA (main device); $V_{GS(amp)peak}$ = 0.8 V.

(1) f = 2496 MHz

(2) f = 2690 MHz

Fig 3. Power gain and drain efficiency as function of output power; typical values

7.6.2 Pulsed CW

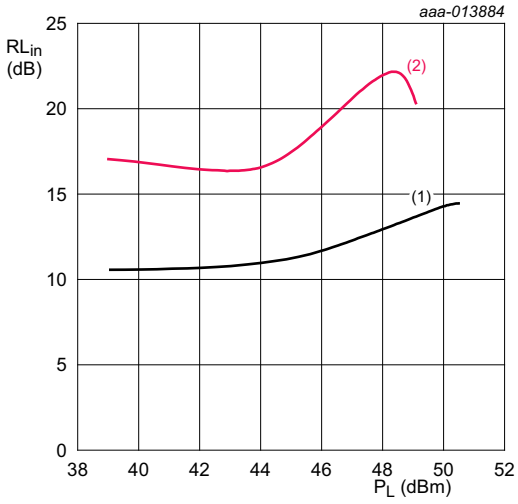


V_{DS} = 28 V; I_{Dq} = 250 mA (main device); $V_{GS(amp)peak}$ = 0.8 V.

(1) f = 2496 MHz

(2) f = 2690 MHz

Fig 4. Power gain and drain efficiency as function of output power; typical values



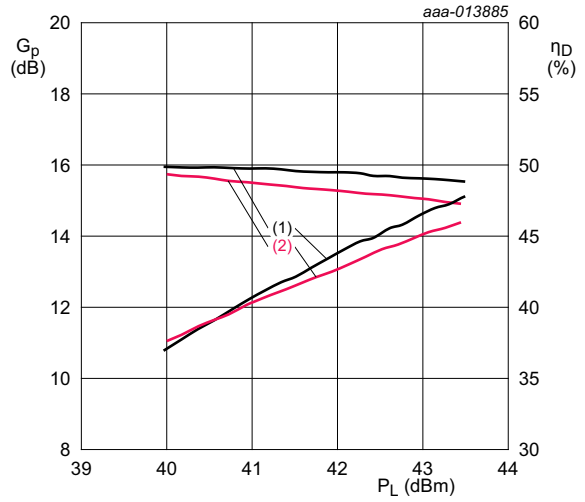
V_{DS} = 28 V; I_{Dq} = 250 mA (main device); $V_{GS(amp)peak}$ = 0.8 V.

(1) f = 2496 MHz

(2) f = 2690 MHz

Fig 5. Input return loss as a function of output power; typical values

7.6.3 1-Carrier W-CDMA

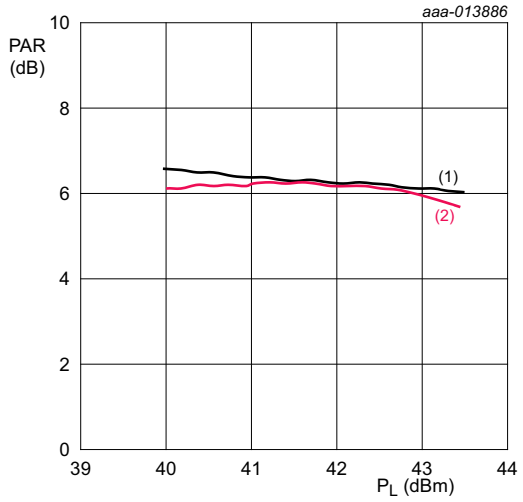


V_{DS} = 28 V; I_{Dq} = 250 mA (main device); $V_{GS(amp)peak}$ = 0.8 V.

(1) f = 2496 MHz

(2) f = 2690 MHz

Fig 6. Power gain and drain efficiency as function of output power; typical values

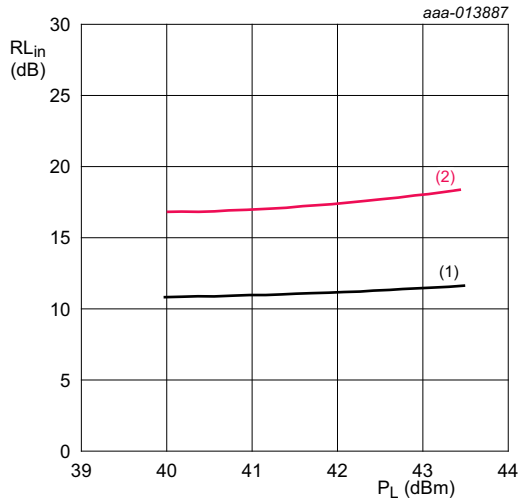


V_{DS} = 28 V; I_{Dq} = 250 mA (main device); $V_{GS(amp)peak}$ = 0.8 V.

(1) f = 2496 MHz

(2) f = 2690 MHz

Fig 7. Peak-to-average power ratio as a function of output power; typical values

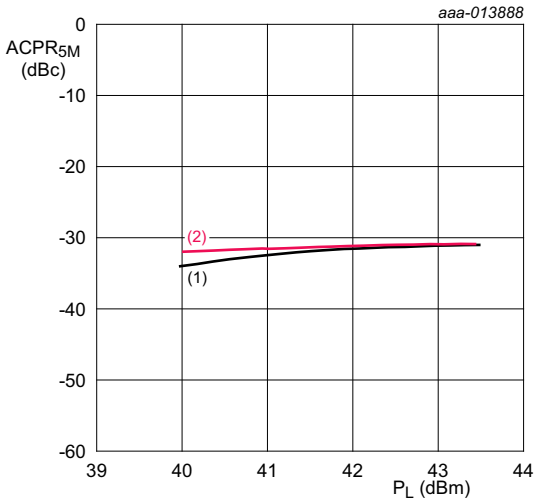


V_{DS} = 28 V; I_{Dq} = 250 mA (main device); $V_{GS(amp)peak}$ = 0.8 V.

(1) f = 2496 MHz

(2) f = 2690 MHz

Fig 8. Input return loss as a function of output power; typical values



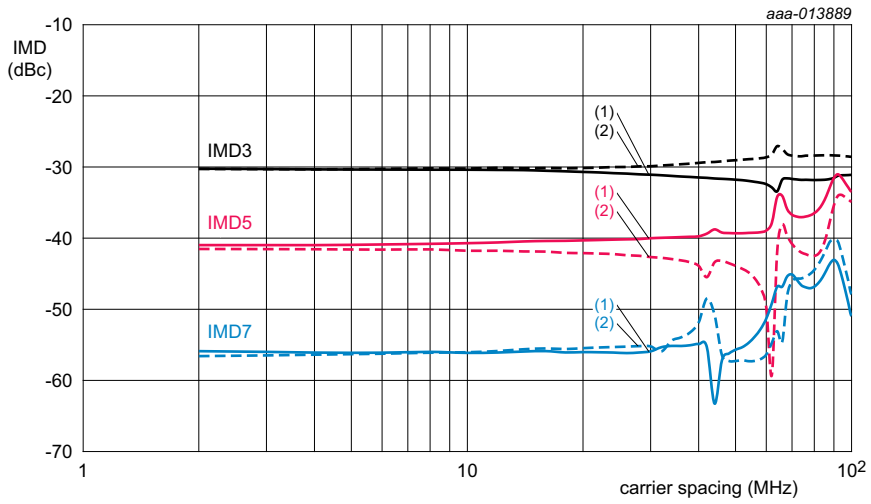
V_{DS} = 28 V; I_{Dq} = 250 mA (main device); $V_{GS(amp)peak}$ = 0.8 V.

(1) f = 2496 MHz

(2) f = 2690 MHz

Fig 9. Adjacent channel power ratio (5 MHz) as a function of output power; typical values

7.6.4 2-Tone VBW



V_{DS} = 28 V; I_{Dq} = 250 mA (main device); f_c = 2600 MHz.

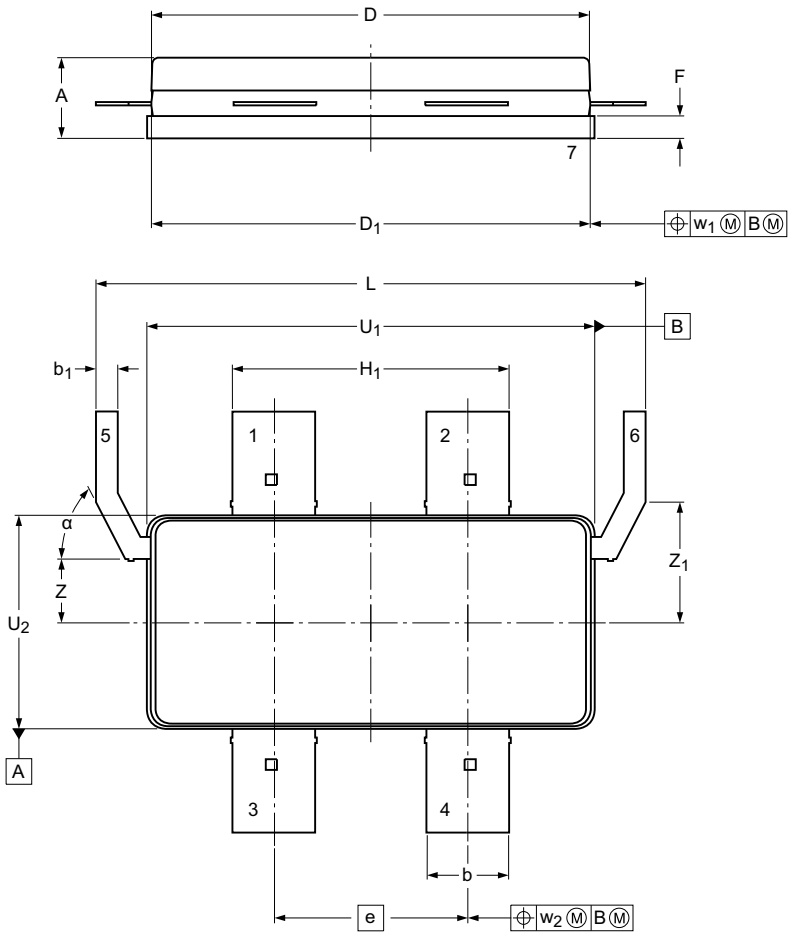
(1) IMD low

(2) IMD high

Fig 10. VBW capability in Doherty demo board

8. Package outline

Air cavity plastic earless flanged package; 6 leads **SOT1275-1**



v	w1	w2
0.5	0.5	0.5

Dimensions (mm dimensions are derived from the original inch dimensions)

Unit		A	b	b_1	c	D	D_1	E	E_1	e	F	H	H_1	L	Q	U_1	U_2	Z	Z_1	α
mm	max	4.01	3.94	1.14	0.178	20.42	20.37	9.80	9.75		1.14	19.53	12.80	25.40	1.68	20.70	9.91	3.67	5.79	65°
	nom									8.89										
	min	3.40	3.68	0.89	0.127	20.12	20.17	9.50	9.55		0.94	19.33	12.60	25.20	1.45	20.50	9.70	3.17	5.29	61°

sot1275-1_po

Outline version	References				European projection	Issue date
	IEC	JEDEC	JEITA			
SOT1275-1						~~13-10-08~~ 14-01-13

Fig 11. Package outline SOT1275-1

9. Handling information

CAUTION

This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the *ANSI/ESD S20.20*, *IEC/ST 61340-5*, *JESD625-A* or equivalent standards.

10. Abbreviations

Table 14. Abbreviations

Acronym	Description
3GPP	3rd Generation Partnership Project
CCDF	Complementary Cumulative Distribution Function
CW	Continuous Wave
DPCH	Dedicated Physical CHannel
ESD	ElectroStatic Discharge
LDMOS	Laterally Diffused Metal-Oxide Semiconductor
LTE	Long Term Evolution
MTF	Median Time to Failure
PAR	Peak-to-Average Ratio
SMD	Surface Mounted Device
VBW	Video BandWidth
VSWR	Voltage Standing Wave Ratio
W-CDMA	Wideband Code Division Multiple Access

11. Revision history

Table 15. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BLC8G27LS-100AV v.2	20140929	Product data sheet	-	BLC8G27LS-100AV v.1
Modifications:	• Section 1.1 on page 1: the frequency range has been changed. • Table 1 on page 1: value $P_{L(AV)}$ changed from 17 W to 18 W • Section 1.3 on page 1: the frequency range has been changed. • Table 5 on page 2: table updated • Section 6 on page 3: section updated • Section 7 on page 4: section added			
BLC8G27LS-100AV v.1	20140225	Objective data sheet	-	-

12. Legal information

12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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13. Contact information

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14. Contents

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Компания «ЭлектроПласт» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits,General Dynamics и др.);

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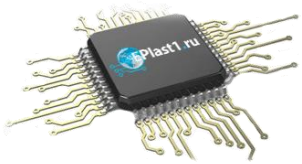
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



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